

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

STK760-213A-E — Single-phase rectification Active Converter Hybrid IC

Overview

This IC is average current control type Active Converter Hybrid IC for power factor improvement of single-phase AC power supply, that containing power devices of step-up active converter, control IC over-current and over-voltage protection circuits.

Applications

• Single-phase rectification active filter for power rectification for air conditioners and general-purpose inverters.

Features

- Power switching device for active converter is adopting IGBT.
- Soft start functions and the over current, the over voltage, and the low-voltage are including as protection circuit
- Capable of controlling ON/OFF by logic level input signal.
- Output voltage changeability functions by control signal.

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STK760-213A-E

Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter		Symbol	Conditions		Ratings	unit	
IGBT	· ·		VCE			600	V
(TR1+TR2)	Repetitive peak collector current		ICP		*1	300	А
	Collector current		IC			105	А
	Power dissipation		PC1			156	W
FRD1	Diode reverse voltag	e	VRM			600	V
(D1)	Repetitive peak forward current		IF1P		*1	110	Α
	Diode forward current		IF1			36	Α
	Power dissipation		PD1			75	W
FRD2	FRD2 Repetitive peak forward current		IF2P		*1	15	А
(D2)	Diode forward currer	nt	IF2			7	А
Power dissipation			PD2			13	W
Supply voltage (V _{CC} -GND)		VCC			20	V	
Signal pin input voltage Pin 4		VIS			-10 to 0.3		
	Pin 5 Pin 8 Pin 9 Pin 2 Pin 6		VCOMP				
			VFB	-0.3 to 6	-0.3 to 6.5		
			VOVP	1			V
			VONF				
			VctI	1		-0.3 to V _{CC}	
Maximum in	put AC voltage		VAC	Single-phase Full-rectified		264	V
Maximum o	utput voltage		٧o	Under the Application condition		450	V
Maximum o	Maximum output power		Wo	(VAC=200V)		6	kW
Input AC current (normal condition)		I _{IN}	1		30	Arms	
Junction temperature		Tj			150	°C	
Operating case temperature		Tc	HIC case temperature	*2	-20 to +100	°C	
Storage temperature		Tstg			-40 to +125	°C	
Tightening torque			A screw part	*3	1.17	N•m	
Withstand voltage		VINS	50Hz sine wave AC 1minute	*4	2000	VRMS	

[Note]

- *1: Duty ratio D = 0.1, tp = 1ms
- *2: Measure point is between 5mm to center of back.
- *3: Torque should be set within 0.79 to 1.17N·m. Flatness of the heat-sink should be lower than 0.2mm.
- *4: The test condition: AC2500V, 1 second.

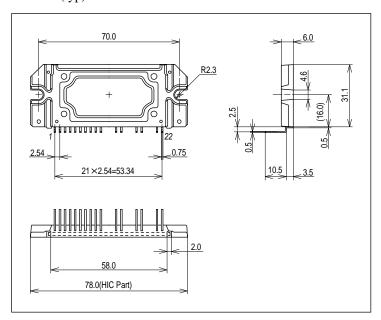
STK760-213A-E

Electrical Characteristics at Tc = 25°C, $V_{CC} = 15.0V$: Unless otherwise noted

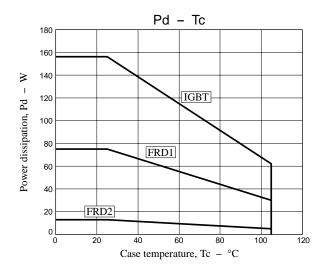
D	0	Conditions	Test circuit	Ratings			
Parameter	Symbol			min	typ	max	unit
Power output part							
Collector-emitter leak current (IGBT)	ICES	V _{CE} = 600V	Fig.1			200	μА
Collector-emitter saturation voltage (IGBT)	V _{CE} (sat)	I _C = 40A	Fig.2		1.2	1.8	V
Diode reverse current (FRD1)	I _R	V _R = 600V	Fig.1			200	μΑ
Diode forward voltage (FRD1)	V _F 1	I _F = 40A	Fig.3		2.2	2.8	V
Diode forward voltage (FRD2)	V _F 2	I _F = 5A	Fig.3		2.5	3.5	V
Junction to case thermal resistance	θј-с1	IGBT (TR1+TR2)			0.80		°C/W
	θј-с2	FRD1 (D1)			1.65		°C/W
	θј-с3	FRD2 (D2)			9.0		°C/W
Control IC part	•	<u> </u>				•	
Control IC input current	I _{CC} (ON)	V _{CC} = 15V, VONF = 5V			14	20	mA
	I _{CC} (OFF)	V _{CC} = 15V, VONF = 0V			2.5	5	
Oscillation frequency	fosc	V _{CC} = 15V, VONF = 5V	Fig.4	19.5	22.0	24.5	kHz
Open loop protection threshold voltage	VOLP			0.8	0.95	1.1	V
Error-amp reference voltage	Vref			4.88	5.0	5.12	V
Peak current protection threshold voltage	VIS(PK)		Fig.5	-0.58	-0.5	-0.42	V
Over voltage protection threshold voltage	VOVP(ON)		Fig.6	5.095	5.3	5.51	V
ON/OFF threshold voltage	VTHON	V _{CC} = 15V	Fig.7	3.0			V
	VTHOFF					0.5	V
Start-up V _{CC} voltage	V _{CC} (ON)	VONF = 5V	F: 0	12.4	13.25	14.1	V
Shut-down V _{CC} voltage	V _{CC} (OFF)		Fig.8	9.4	10.0	10.7	V
Substrate temperature monitor resistance	RTH	Resistance between VTH-GND	Fig.3	90	100	110	kΩ
Application circuit : VAC = 200V, VO =	380V (Vctl = 1.5	507V)					
Output voltage	Vo	Wo = 2kW		366	380	394	V
Power Factor	cosφ	Wo = 400W	Fig.9	0.98	0.99		
		Wo = 2kW		0.99	0.995	1.0	

Package Dimensions

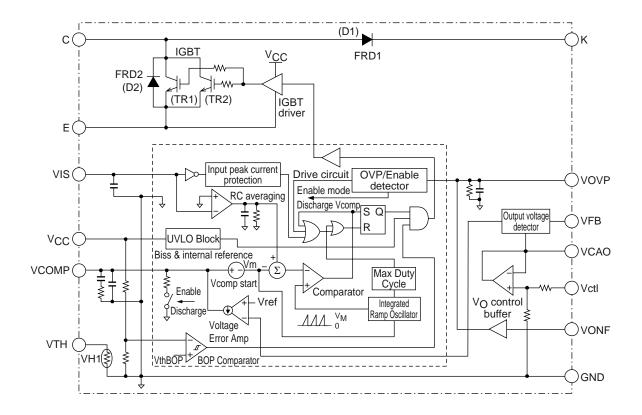
unit:mm (typ)



IGBT (TR1+TR2), FRD1 (D1) & FRD2 (D2) vs. Temperature Derating (Ta = 25°C)



Block Diagram



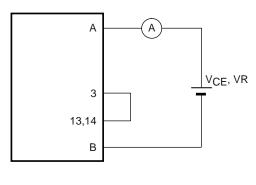
Explanation of Terminal

Terminal No.	Symbol	Explanation
1	Vcc	Control IC power supply input
2	VONF	ON/OFF control terminal
3	GND	Signal GND
4	VIS	Current detection terminal
5	VCOMP	Phase compensation terminal (Voltage error amplifier out)
6	Vctl	Output voltage control signal input
7	VCAO	Output voltage control amplifier output
8	VFB	Output voltage feed back terminal
9	VOVP	Over voltage protection terminal
10	VTH	Terminal of thermistor TH1
11, 12	-	An empty terminal
13, 14	Е	IGBT (TR1+TR2) Emitter
15, 16	-	An empty terminal
17, 18	С	IGBT (TR1+TR2) Collector
19, 20	-	An empty terminal
21, 22	K	FRD1 (D1) Cathode

Test Circuit -1

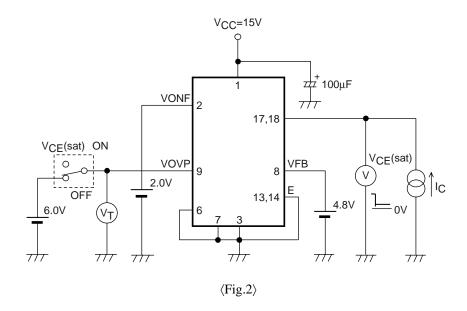
(1) ICES, I_R

	IGBT	FRD1
А	17, 18	21, 22
В	13, 14	17, 18



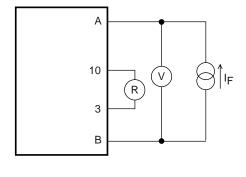
 $\langle Fig.1 \rangle$

(2) VCE(sat) (Test by Pulse)



(3) V_F1, V_F2 (Test by Pulse), RTH

	FRD1	FRD2
Α	17, 18	13, 14
В	21, 22	17, 18

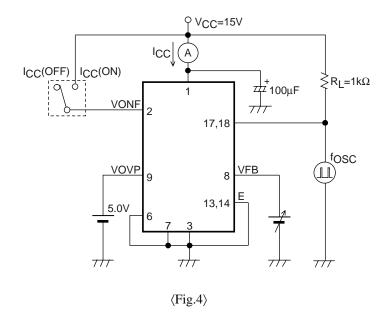


 $\langle Fig.3 \rangle$

Test Circuit -2

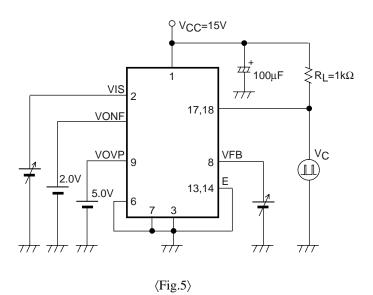
(4) $I_{CC}(ON)/I_{CC}(OFF)$, VOLP, f_{OSC}

Icc, fosc	VOLP
VFB = 1.1V	VONF = 5.0V

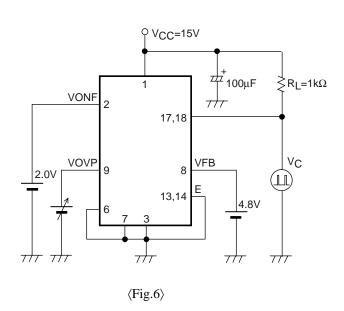


(5) Vref, VIS(PK)

Vref	VIS(PK)	
VIS = -0.6V	VFB = 4.8V	

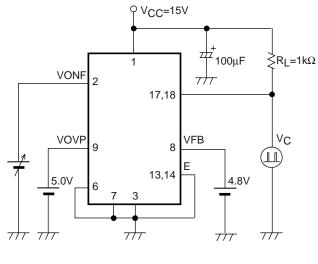


(6) VOVP(ON)



Test Circuit -3

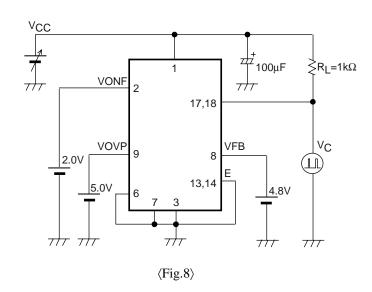
(7) VTHON, VTHOFF



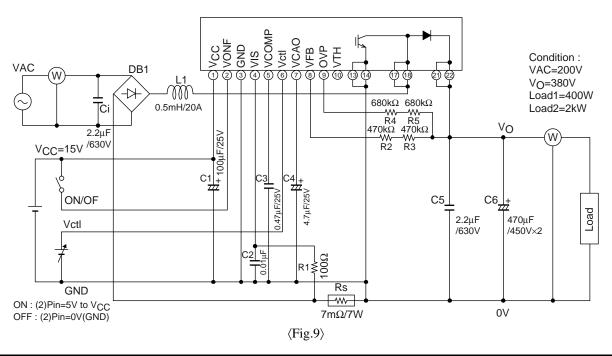
⟨Fig.7⟩

(8) $V_{CC}(ON)$, $V_{CC}(OFF)$

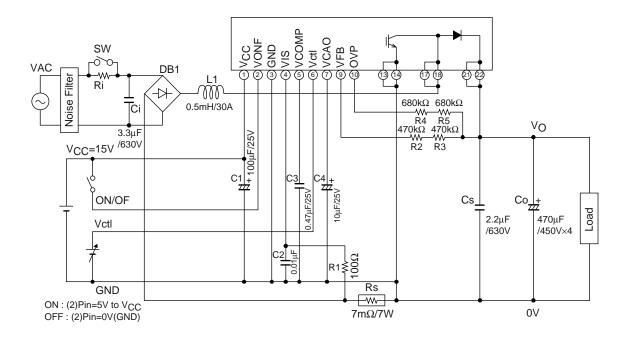
V _{CC} (ON)	V _{CC} (OFF)
Vc-ON	Vc-OFF



(9) Power Factor (COS\$\phi\$)



Application Circuit

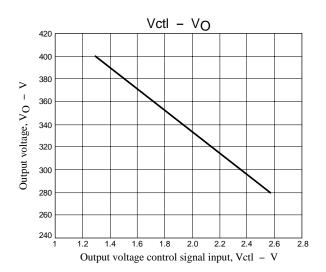


Recommended Condition

Parameter	Symbol	Conditions	Ratings	unit
AC Voltage	VAC	50/60Hz	170 to 264	Vrms
Output voltage	VO		VAC×√2+(10 to 15)≤450	V
Over-voltage detection voltage	VOV		V _{OUT} +(10 to 20)	V
Control IC supply voltage	VCC	V _{CC} -GND	14.5 to 17.0	V
Inductor	L1		0.5	mH
Input film capacitor	Ci		3.3≤Ci	μF
Output film capacitor	Cs		2.2≤Cs	μF
Output electrolytic capacitor	Co		1880≤Co	μF

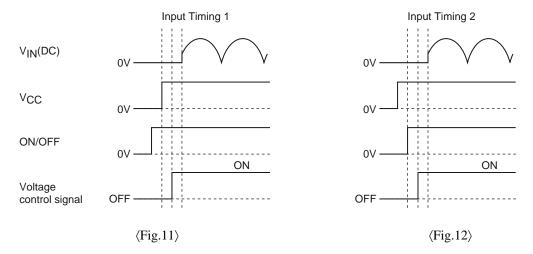
Output Voltage Control

Output voltage control signal Vctl sets referring to the Vctl-VO characteristic of the figure below.

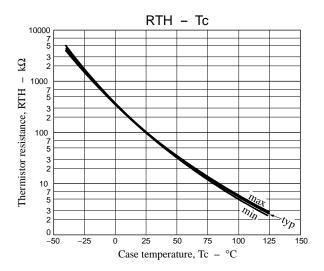


Timing Chart

Even if power supply and signal at any timing are input, this IC is not destroyed. However, soft start circuit doesn't operate when $V_{IN}(DC)$ is input at the timing of Figure 11 and 12. Therefore, overcurrent protection circuit will operate, and audio frequency noise from coil may generate. Please turn on ON/OFF or V_{CC} after $V_{IN}(DC)$ to avoid this.



The built-in thermistor resistance temperature characteristic



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